

The InAsSb-based SACM APD with hole-initiated multiplication

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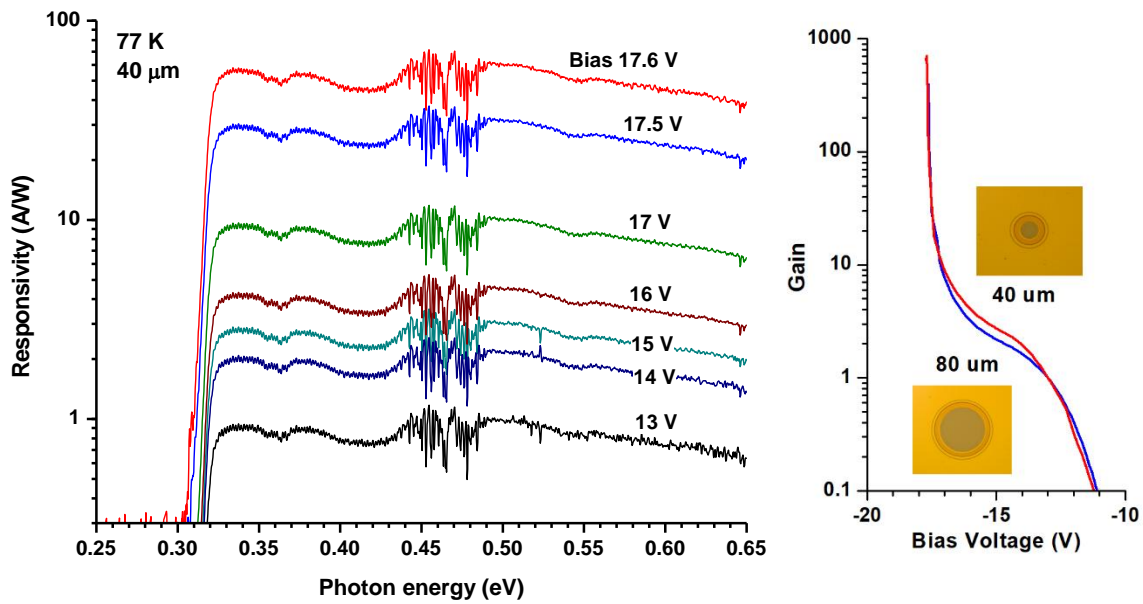


Figure 1. Spectra of the current responsivity measured at 77 K for 40 μm diameter mesa device at bias voltages from -13 to -17.6 V. The inset shows the dependences of the multiplication gain on bias voltage measured for devices with 40 and 80 μm mesa diameter.